

**Notice of References Cited**Application/Control No.  
10/014,466Applicant(s)/Patent Under  
Reexamination  
SAMOILOV ET AL.Examiner  
Robert M KunemundArt Unit  
1765

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.